

C. Material Growth & Characterization 분과

2020년 2월 14일(금), 10:45-12:30 / Room F (스페이스 I, 6층)

■ [FF2-C] Wide Bandgap Materials II (SiC, diamond & etc)

좌장: 이기영 박사 (삼성종합기술원)

FF2-C-1 10:45-11:15	[초청] Development Status of SiC Single Crystal Substrate for Power Device Application Won Jae Lee <i>Department of Advanced Materials Engineering, Dong-Eui University</i>
FF2-C-2 11:15-11:45	[초청] Process Design of Bulk Crystal Growth of SiC and Other Wide Bandgap Semiconductors Seong-Min Jeong <i>KICET</i>
FF2-C-3 11:45-12:00	Overgrowth of Single Crystal CVD Diamond Using Defect-selective Etching Technique Jonggeon Lee ¹ , Taemyung Kwak ¹ , Geunho Yoo ¹ , Seong-woo Kim ² , and Okhyun Nam ¹ <i>¹Department of Nano-Optical Engineering, Korea Polytechnic University, ²Adamant Namiki Precision Jewel Co. Ltd.</i>
FF2-C-4 12:00-12:15	Boron-doping of Single Crystal Diamond Semiconductor Using Microwave Plasma Chemical Vapor Deposition Taemyung Kwak ¹ , Geunho Yoo ¹ , Jonggun Lee ¹ , Uiho Choi ¹ , Byeongchan So ¹ , Seong-woo Kim ² , and Okhyun Nam ¹ <i>¹Department of Nano-Optical Engineering, Korea Polytechnic University, ²Adamant Namiki Precision Jewel Co. Ltd</i>
FF2-C-5 12:15-12:30	Theoretical Understanding and Design of High Dielectric Constant (Be,Mg)O Solid Solution Gyuseung Han ^{1,2} , In Won Yeu ^{1,2} , Cheol Seong Hwang ² , and Jung-Hae Choi ¹ <i>¹Center for Electronic Materials, KIST, ²Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University</i>